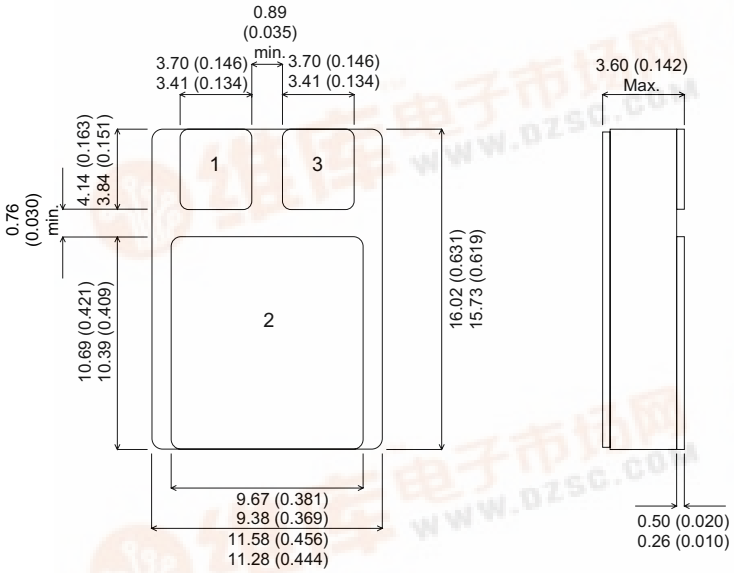
SEME LAB

IRF150SMD

MECHANICAL DATA

Dimensions in mm (inches)



SMD1 PACKAGE

Pad 1 – Gate Pad 2 – Drain Pad 3 – Source

N–CHANNEL POWER MOSFET

V_{DSS}	100V
$I_{D(cont)}$	19A
$R_{DS(on)}$	0.070Ω

FEATURES

- HERMETICALLY SEALED SURFACE MOUNT PACKAGE
- SMALL FOOTPRINT – EFFICIENT USE OF PCB SPACE.
- SIMPLE DRIVE REQUIREMENTS
- LIGHTWEIGHT
- HIGH PACKING DENSITIES

Note: IRFNxxx also available with pins 1 and 3 reversed.

ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C unless otherwise stated)

V_{GS}	Gate – Source Voltage		±20V
I_D	Continuous Drain Current	(V_{GS} = 0 , T_{case} = 25°C)	27A
I_D	Continuous Drain Current	(V_{GS} = 0 , T_{case} = 100°C)	19A
I_{DM}	Pulsed Drain Current [1]		108A
P_D	Power Dissipation @ T_{case} = 25°C		100W
	Linear Derating Factor		0.8W/°C
E_{AS}	Single Pulse Avalanche Energy [2]		150mJ
dv/dt	Peak Diode Recovery [3]		5.5V/ns
T_J , T_{stg}	Operating and Storage Temperature Range		–55 to 150°C
T_L	Package Mounting Surface Temperature (for 5 sec)		300°C
$R_{\theta JC}$	Thermal Resistance Junction to Case		1.25°C/W
$R_{\theta J–PCB}$	Thermal Resistance Junction to PCB (Typical)		3°C/W

Notes

1) Pulse Test: Pulse Width ≤ 300ms, δ ≤ 2%

2) @ V_{DD} = 25V , L ≥ 0.3mH , R_G = 25Ω , Peak I_L = 27A , Starting T_J = 25°C

3) @ I_{SD} ≤ 27A , di/dt ≤ 70A/µs , V_{DD} ≤ BV_{DSS} , T_J ≤ 150°C , SUGGESTED R_G = 2.35Ω

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ELECTRICAL CHARACTERISTICS (T_{amb} = 25°C unless otherwise stated)

	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
	STATIC ELECTRICAL RATINGS					
BV_{DSS}	Drain – Source Breakdown Voltage	V_{GS} = 0 I_D = 1mA	100			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Temperature Coefficient of Breakdown Voltage	Reference to 25°C I_D = 1mA		0.13		V/°C
$R_{DS(on)}$	Static Drain – Source On–State Resistance [1]	V_{GS} = 10V I_D = 19A			0.070	Ω
		V_{GS} = 10V I_D = 27A			0.081	
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS} I_D = 250µA	2		4	V
g_{fs}	Forward Transconductance [1]	V_{DS} ≥ 15V I_{DS} = 19A	9			S(℧)
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS} = 0 V_{DS} = 0.8BV_{DSS}			25	µA
		T_J = 125°C			250	
I_{GSS}	Forward Gate – Source Leakage	V_{GS} = 20V			100	nA
I_{GSS}	Reverse Gate – Source Leakage	V_{GS} = –20V			–100	
	DYNAMIC CHARACTERISTICS					
C_{iss}	Input Capacitance	V_{GS} = 0		3700		pF
C_{oss}	Output Capacitance	V_{DS} = 25V		1100		
C_{rss}	Reverse Transfer Capacitance	f = 1MHz		200		
Q_g	Total Gate Charge [1]	V_{GS} = 10V I_D = 27A V_{DS} = 0.5BV_{DSS}	50		125	nC
Q_{gs}	Gate – Source Charge [1]	I_D = 27A	8		22	nC
Q_{gd}	Gate – Drain (“Miller”) Charge [1]	V_{DS} = 0.5BV_{DSS}	15		65	
$t_{d(on)}$	Turn–On Delay Time	V_{DD} = 50V I_D = 27A R_G = 2.35Ω			35	ns
t_r	Rise Time				190	
$t_{d(off)}$	Turn–Off Delay Time				170	
t_f	Fall Time				130	
	SOURCE – DRAIN DIODE CHARACTERISTICS					
I_S	Continuous Source Current				27	A
I_{SM}	Pulse Source Current [2]				108	
V_{SD}	Diode Forward Voltage	I_S = 27A T_J = 25°C V_{GS} = 0			1.8	V
t_{rr}	Reverse Recovery Time	I_F = 27A T_J = 25°C			500	ns
Q_{rr}	Reverse Recovery Charge	d_i / d_t ≤ 100A/µs V_{DD} ≤ 50V			2.9	µC
t_{on}	Forward Turn–On Time			Negligible		
	PACKAGE CHARACTERISTICS					
L_D	Internal Drain Inductance (from centre of drain pad to die)			0.8		nH
L_S	Internal Source Inductance (from centre of source pad to end of source bond wire)			2.8		

Notes

1) Pulse Test: Pulse Width ≤ 300ms, δ ≤ 2%

2) Repetitive Rating – Pulse width limited by maximum junction temperature.